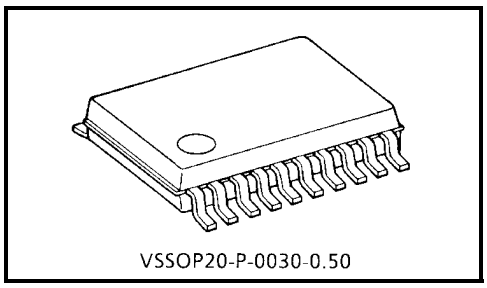
TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MH540FK, TC7MH541FK

Octal Bus Buffer

TC7MH540FK Inverted, 3-State Outputs

TC7MH541FK Non-Inverted, 3-State Outputs



Weight: 0.03 g (typ.)

The TC7MH540FK and TC7MH541FK are advanced high speed CMOS octal bus buffers fabricated with silicon gate C^2MOS technology.

They achieve the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

The TC7MH540FK is an inverting type, and the TC7MH541FK is a non-inverting type.

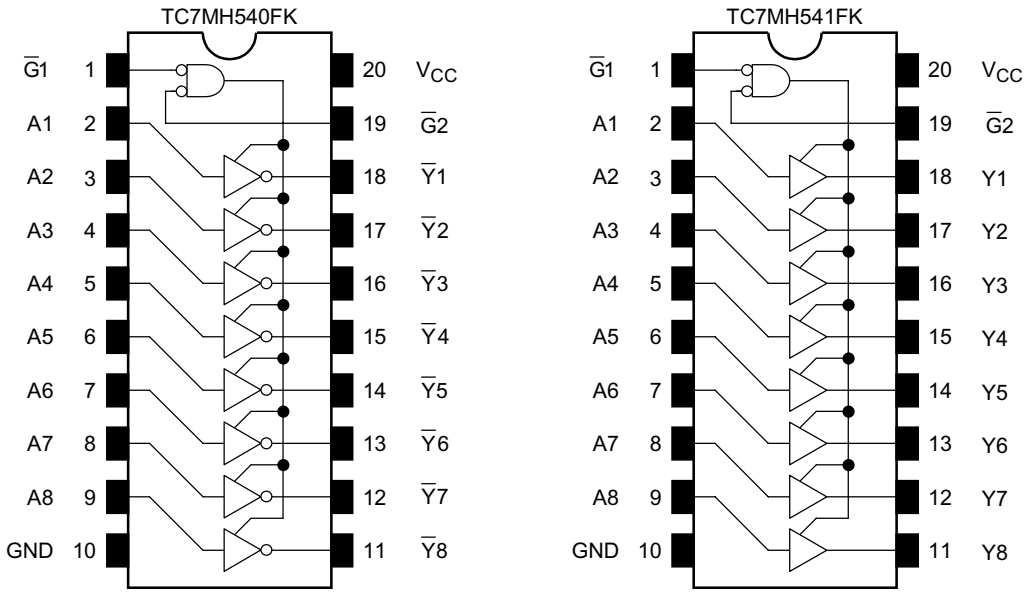
When either $\overline{G}1$ or $\overline{G}2$ are high, the terminal outputs are in the high-impedance state.

An input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

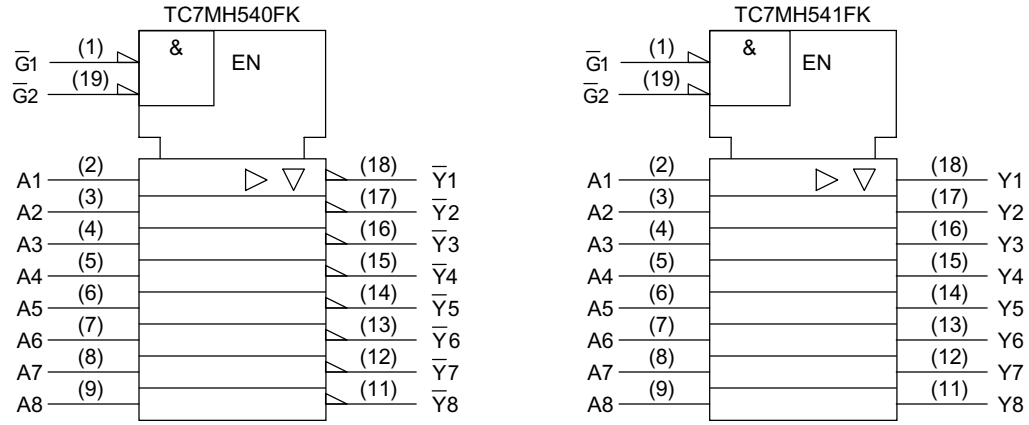
Features

- High speed: t_{pd} = 3.7 ns (typ.) (V_{CC} = 5 V)
- Low power dissipation: I_{CC} = 4 μA (max) (Ta = 25°C)
- High noise immunity: $V_{NIH} = V_{NIL}$ = 28% V_{CC} (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: $t_{pLH} \simeq t_{pHL}$
- Wide operating voltage range: $V_{CC\ (opr)}$ = 2~5.5 V
- Low noise: V_{OLP} = 1.0 V (max)
- Pin and function compatible with 74ALS540/541

Pin Assignment (top view)



IEC Logic Symbol



Truth Table

Inputs			Outputs	
$\overline{G}1$	$\overline{G}2$	A_n	Y_n (541)	$\overline{Y}_n$ (540)
H	X	X	Z	Z
X	H	X	Z	Z
L	L	H	H	L
L	L	L	L	H

X: Don't care

Z: High impedance

Y_n: TC7MH541

$\overline{Y}_n$: TC7MH540

Maximum Ratings

Characteristics	Symbol	Rating	Unit
Supply voltage range	V_{CC}	−0.5~7.0	V
DC input voltage	V_{IN}	−0.5~7.0	V
DC output voltage	V_{OUT}	−0.5~V_{CC} + 0.5	V
Input diode current	I_{IK}	−20	mA
Output diode current	I_{OK}	±20	mA
DC output current	I_{OUT}	±25	mA
DC V_{CC}/ground current	I_{CC}	±75	mA
Power dissipation	P_D	180	mW
Storage temperature	T_{stg}	−65~150	°C

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit
Supply voltage	V_{CC}	2.0~5.5	V
Input voltage	V_{IN}	0~5.5	V
Output voltage	V_{OUT}	0~V_{CC}	V
Operating temperature	T_{opr}	−40~85	°C
Input rise and fall time	dt/dv	0~100 (V_{CC} = 3.3 ± 0.3 V) 0~20 (V_{CC} = 5 ± 0.5 V)	ns/V

Electrical Characteristics

DC Characteristics

Characteristics		Symbol	Test Condition			Ta = 25°C			Ta = −40~85°C		Unit
					V_{CC} (V)	Min	Typ.	Max	Min	Max	
Input voltage	High level	V_{IH}	—		2.0	1.50	—	—	1.50	—	V
					3.0~5.5	$V_{CC} \times 0.7$	—	—	$V_{CC} \times 0.7$	—	
	Low level	V_{IL}	—		2.0	—	—	0.50	—	0.50	
					3.0~5.5	—	—	$V_{CC} \times 0.3$	—	$V_{CC} \times 0.3$	
Output voltage	High level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -50$ μA	2.0	1.9	2.0	—	1.9	—	V
					3.0	2.9	3.0	—	2.9	—	
					4.5	4.4	4.5	—	4.4	—	
				$I_{OH} = -4$ mA	3.0	2.58	—	—	2.48	—	
				$I_{OH} = -8$ mA	4.5	3.94	—	—	3.80	—	
	Low level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 50$ μA	2.0	—	0	0.1	—	0.1	
					3.0	—	0	0.1	—	0.1	
					4.5	—	0	0.1	—	0.1	
				$I_{OL} = 4$ mA	3.0	—	—	0.36	—	0.44	
				$I_{OL} = 8$ mA	4.5	—	—	0.36	—	0.44	
3-state output off-state current		I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND		5.5	—	—	±0.25	—	±2.50	μA
Input leakage current		I_{IN}	$V_{IN} = 5.5$ V or GND		0~5.5	—	—	±0.1	—	±1.0	μA
Quiescent supply current		I_{CC}	$V_{IN} = V_{CC}$ or GND		5.5	—	—	4.0	—	40.0	μA

AC Characteristics (Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = −40~85°C		Unit
			V_{CC} (V)	C_L (pF)	Min	Typ.	Max	Min	Max	
Propagation delay time (TC7MH540FK)	t_{pLH} t_{pHL}	—	3.3 ± 0.3	15	—	4.8	7.0	1.0	8.5	ns
				50	—	7.3	10.5	1.0	12.0	
			5.0 ± 0.5	15	—	3.7	5.0	1.0	6.0	
				50	—	5.2	7.0	1.0	8.0	
Propagation delay time (TC7MH541FK)	t_{pLH} t_{pHL}	—	3.3 ± 0.3	15	—	5.0	7.0	1.0	8.5	ns
				50	—	7.5	10.5	1.0	12.0	
			5.0 ± 0.5	15	—	3.5	5.0	1.0	6.0	
				50	—	5.0	7.0	1.0	8.0	
3-state output enable time	t_{pZL} t_{pZH}	R_L = 1 kΩ	3.3 ± 0.3	15	—	6.8	10.5	1.0	12.5	ns
				50	—	9.3	14.0	1.0	16.0	
			5.0 ± 0.5	15	—	4.7	7.2	1.0	8.5	
				50	—	6.2	9.2	1.0	10.5	
3-state output disable time	t_{pLZ} t_{pHZ}	R_L = 1 kΩ	3.3 ± 0.3	50	—	11.2	15.4	1.0	17.5	ns
			5.0 ± 0.5	50	—	6.0	8.8	1.0	10.0	
Output to output skew	t_{osLH} t_{osHL}	(Note1)	3.3 ± 0.3	50	—	—	1.5	—	1.5	ns
			5.0 ± 0.5	50	—	—	1.0	—	1.0	
Input capacitance	C_{IN}	—			—	4	10	—	10	pF
Output capacitance	C_{OUT}	—			—	6	—	—	—	pF
Power dissipation capacitance (Note2)	C_{PD}	TC7MH540FK			—	17	—	—	—	pF
		TC7MH541FK			—	18	—	—	—	

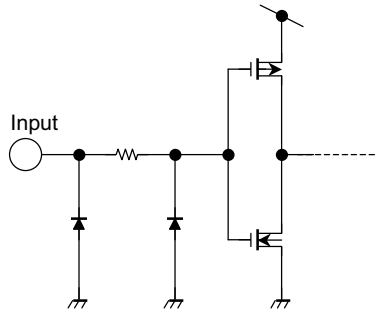
Note1: Parameter guaranteed by design.
$t_{osLH} = |t_{pLHm} - t_{pLHn}|$, $t_{osHL} = |t_{pHLm} - t_{pHLn}|$

Note2: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.
Average operating current can be obtained by the equation:
$I_{CC\ (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/8$ (per bit)

Noise Characteristics (Input: $t_r = t_f = 3$ ns)

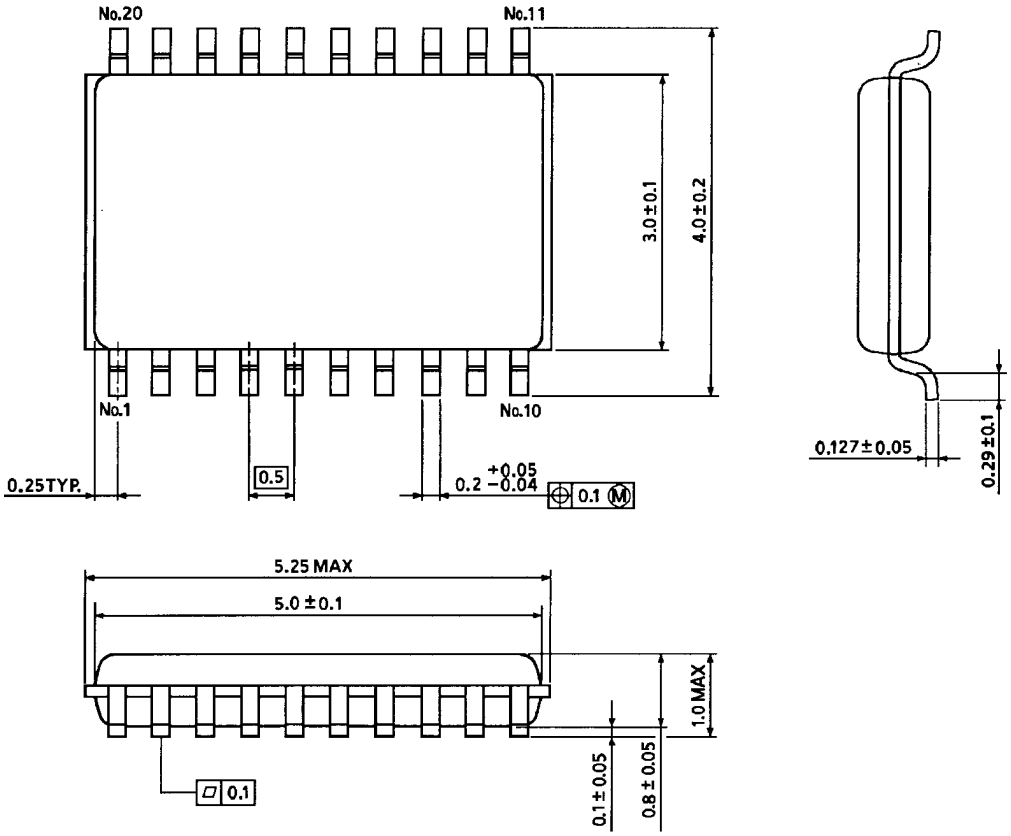
Characteristics	Symbol	Test Condition	Ta = 25°C			Unit
			V_{CC} (V)	Typ.	Limit	
Quiet output maximum dynamic V_{OL}	V_{OLP}	C_L = 50 pF	5.0	0.7	1.0	V
Quiet output minimum dymnamic V_{OL}	V_{OLV}	C_L = 50 pF	5.0	−0.7	−1.0	V
Minimum high level dynamic input voltage V_{IH}	V_{IHD}	C_L = 50 pF	5.0	—	1.5	V
Maximum low level dynamic input voltage V_{IL}	V_{ILD}	C_L = 50 pF	5.0	—	3.5	V

Input Equivalent Circuit



Package Dimensions

VSSOP20-P-0030-0.50 Unit : mm



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